

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A substrate processing apparatus comprising:
a substrate holding mechanism for holding a substrate under a holding force which is
produced due to a centrifugal force caused by rotation ~~changed according to a rotational speed of~~
said substrate holding mechanism;
a substrate rotation mechanism for rotating said substrate holding mechanism to rotate the
substrate held by said substrate holding mechanism; ~~and~~
a driving device for changing a rotational speed of said substrate holding mechanism so
as to change the holding force under which the substrate is held by said substrate holding
mechanism; and
a treatment liquid supply mechanism for supplying a treatment liquid to a desired portion
of the substrate held by said substrate holding mechanism.

2. (Cancelled)

3. (Currently Amended) A substrate processing apparatus comprising:
a substrate holding mechanism for holding a peripheral portion of a substrate;
a base member having said substrate holding mechanism attached thereto, said base
member facing at least one surface of the substrate;
a rotatable shaft attached to a central portion of said base member;
a first liquid supply nozzle for selectively supplying a chemical liquid or a first cleaning
liquid to the substrate;
a switching device for switching the chemical liquid and the first cleaning liquid to be
supplied to said first nozzle;
a second liquid supply nozzle for supplying a second cleaning liquid to an inner surface
of said substrate holding mechanism and an upper surface of said base member;
a gas supply nozzle for supplying a gas to a space between the substrate and said base
member; ~~and~~
a nozzle structure including said first liquid supply nozzle, said second liquid supply
nozzle, and said gas supply nozzle, said nozzle structure being disposed within said rotatable
shaft; and

a purge gas supply line for supplying a purge gas to a gap between said rotatable shaft and said nozzle structure.

4. (Original) The substrate processing apparatus as recited in claim 3, wherein said first liquid supply nozzle is configured to clean said first liquid supply nozzle, an outer surface of said nozzle structure, and vicinity thereof with the first cleaning liquid.

5. (Original) The substrate processing apparatus as recited in claim 3, further comprising:

a first line connected to said first liquid supply nozzle;
a second line connected to said second liquid supply nozzle; and
a liquid discharge mechanism for discharging a liquid remaining in said first line and said second line.

6. (Cancelled)

7. (Original) The substrate processing apparatus as recited in claim 3, further comprising a third liquid supply nozzle for supplying a third cleaning liquid to an outer surface of said substrate holding mechanism.

8. (Currently Amended) The substrate processing apparatus as recited in ~~any one of claims 1 through 7~~ claim 1, further comprising a scatter prevention cup disposed outside of said substrate holding mechanism so as to cover said substrate holding mechanism, said scatter prevention cup being movable in a vertical direction.

9. (Currently Amended) A substrate processing method comprising:

holding a substrate by a substrate holding mechanism under a holding force which is produced due to a centrifugal force caused by rotation of the substrate holding mechanism;

rotating the substrate holding mechanism by a substrate rotation mechanism to rotate the substrate; ~~and~~

changing a rotational speed of the substrate holding mechanism so as to change the holding force under which the substrate is held by the substrate holding mechanism; and

supplying a treatment liquid to a desired portion of the rotating substrate to process the substrate while said changing a rotational speed of the substrate holding mechanism ~~and a rotational speed of the substrate relative to each other.~~

10. (Currently Amended) The substrate processing method as recited in claim 9, wherein said changing a rotational speed of the substrate holding mechanism ~~and a rotational speed of the substrate relative to each other~~ comprises:

increasing or decreasing the rotational speed of the substrate holding mechanism to change the rotational speed of the substrate holding mechanism and the rotational speed of the substrate relative to each other.

11. (Currently Amended) The substrate processing method as recited in claim 10, wherein said changing a rotational speed of the substrate holding mechanism ~~and a rotational speed of the substrate relative to each other~~ further comprises:

stopping said supplying the substrate treatment liquid simultaneously with or after said increasing or decreasing the rotational speed of the substrate holding mechanism.

12. (Currently Amended) The substrate processing method as recited in claim 9, wherein said changing a rotational speed of the substrate holding mechanism ~~and a rotational speed of the substrate relative to each other~~ comprises:

changing the rotational speed of the substrate holding mechanism from a first rotational speed to a second rotational speed; and then

returning the rotational speed of the substrate holding mechanism from the second rotational speed to the first rotational speed.

13. (Original) A substrate processing method comprising:

holding a substrate by a substrate holding mechanism;

rotating the substrate holding mechanism by a substrate rotation mechanism to rotate the substrate;

supplying a treatment liquid to the rotating substrate to process the substrate;
rotating the substrate at a first high rotational speed after said supplying the treatment liquid;

supplying a cleaning liquid to at least one surface of the substrate rotated at the first high rotational speed to clean the treatment liquid attached to the substrate; and

removing a chemical liquid attached to at least one of the substrate holding mechanism and the substrate rotation mechanism in a state such that the at least one surface of the substrate is covered with the cleaning liquid.

14. (Original) The substrate processing method as recited in claim 13, wherein the first high rotational speed is in a range of 1000 to 3000 rpm.

15. (Original) The substrate processing method as recited in claim 13, further comprising rotating the substrate at a second high rotational speed to remove the cleaning liquid and dry the substrate.

16. (Original) The substrate processing method as recited in claim 15, wherein said rotating the substrate at a second high rotational speed comprises rotating the substrate at a high rotational speed substantially equal to the first high rotational speed for a desired period of time.

17. (Original) A substrate processing method comprising:
holding a substrate by a substrate holding mechanism;
rotating the substrate holding mechanism by a substrate rotation mechanism to rotate the substrate;

supplying a treatment liquid to the rotating substrate to process the substrate; and
supplying a cleaning liquid to the rotating substrate to clean the substrate holding mechanism.

18. (Original) The substrate processing method as recited in claim 17, wherein said rotating the substrate holding mechanism comprises rotating the substrate holding mechanism at a rotational speed lower than 300 rpm during said supplying the cleaning liquid.

19. (Original) A substrate processing method comprising:
holding a substrate by a substrate holding mechanism;
rotating the substrate holding mechanism by a substrate rotation mechanism to rotate the substrate;
supplying a treatment liquid to the rotating substrate to process the substrate;
rotating the substrate at a first high rotational speed after supplying the treatment liquid;
supplying a cleaning liquid to at least one surface of the substrate rotated at the first high rotational speed to clean the treatment liquid attached to the substrate;
removing a chemical liquid attached to at least one of the substrate holding mechanism and the substrate rotation mechanism in a state such that the at least one surface of the substrate is covered with the cleaning liquid;
supplying a cleaning liquid to the rotating substrate to clean the substrate holding mechanism; and
rotating the substrate at a second rotational speed substantially equal to the first high rotational speed for a desired period of time to remove the cleaning liquid and dry the substrate.

20. (Currently Amended) The substrate processing method as recited in ~~any one of claims 13 through 19~~ claim 13, wherein the cleaning liquid comprises pure water, deaerated water, or gas dissolved water.

21. (Currently Amended) The substrate processing method as recited in ~~any one of claims 9 through 20~~ claim 9, wherein supplying the treatment liquid comprises supplying the treatment liquid to a peripheral portion of the substrate to remove a film formed on the peripheral portion of the substrate.

22. (Original) The substrate processing method as recited in claim 21, wherein the film to be removed comprises a film containing one of Cu, Co, Co alloy, Ta, Ta-N, W, W-N, Ti, Ti-N, Ni, Ru, P, B, and Mo, or a film having a plurality of layers each containing one of Cu, Co, Co alloy, Ta, Ta-N, W, W-N, Ti, Ti-N, Ni, Ru, P, B, and Mo.

23. (Currently Amended) A substrate processing method comprising:
holding a substrate by a substrate holding mechanism;
rotating the substrate holding mechanism by a substrate rotation mechanism to rotate the substrate;
supplying a treatment liquid to the rotating substrate to process the substrate;
supplying a chemical liquid from a first liquid supply nozzle to the substrate;
switching a liquid to be supplied from the first liquid supply nozzle into a cleaning liquid;
supplying the cleaning liquid to the substrate;
supplying a cleaning liquid to the first liquid supply nozzle and vicinity of the first liquid supply nozzle to clean the first liquid supply nozzle and vicinity of the first liquid supply nozzle;
and
rotating the substrate holding mechanism to remove a liquid attached to the substrate and dry the substrate; and
supplying a gas from a gas supply nozzle to a space between the substrate and a base member having the substrate holding mechanism attached thereon during said drying the substrate.

24. (Original) The substrate processing method as recited in claim 23, further comprising:
stopping said supplying the cleaning liquid; and
discharging a liquid remaining in the first liquid supply nozzle and a line connected to the first liquid supply nozzle after said stopping and before said drying the substrate.

25. (Original) The substrate processing method as recited in claim 23, further comprising:
supplying a cleaning liquid from a second liquid supply nozzle, before said drying the substrate, to clean an inner surface of the substrate holding mechanism and an upper surface of a base member having the substrate holding mechanism attached thereon.

26. (Cancelled)

27. (Currently Amended) The substrate processing method as recited in claim-~~26~~ 23, further comprising:

supplying the gas from the gas supply nozzle to the space between the substrate and the base member during said cleaning the first liquid supply nozzle and the vicinity thereof.

28. (New) The substrate processing method as recited in claim 13, wherein said removing the chemical liquid comprises removing a chemical liquid attached to a scatter prevention cup disposed so as to surround the substrate holding mechanism.

29. (New) The substrate processing method as recited in claim 17, wherein said supplying the chemical liquid comprises removing a chemical liquid attached to a scatter prevention cup disposed so as to surround the substrate holding mechanism.

30. (New) The substrate processing apparatus as recited in claim 3, further comprising a scatter prevention cup disposed outside of said substrate holding mechanism so as to cover said substrate holding mechanism, said scatter prevention cup being movable in a vertical direction.

31. (New) The substrate processing method as recited claim 17, wherein the cleaning liquid comprises pure water, deaerated water, or gas dissolved water.

32. (New) The substrate processing method as recited claim 19, wherein the cleaning liquid comprises pure water, deaerated water, or gas dissolved water.

33. (New) The substrate processing method as recited claim 13, wherein supplying the treatment liquid comprises supplying the treatment liquid to a peripheral portion of the substrate to remove a film formed on the peripheral portion of the substrate.

34. (New) The substrate processing method as recited claim 17, wherein supplying the treatment liquid comprises supplying the treatment liquid to a peripheral portion of the substrate to remove a film formed on the peripheral portion of the substrate.

35. (New) The substrate processing method as recited in claim 19, wherein supplying the treatment liquid comprises supplying the treatment liquid to a peripheral portion of the substrate to remove a film formed on the peripheral portion of the substrate.